

A theoretical study of electron drift mobility anisotropy in n-type 4H- and 6H-SiC

Velmre, Enn; Udal, Andres Proceedings of the International Conference on Silicon Carbide and Related Materials - 1999 (ICSCRM'99) : Research Triangle Park, North-Carolina, USA, Oct. 10-15, 1999. Vol. 1 2000 / p. 725-728

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